

Silicon NPN Power Transistors

2SC2336 2SC2336A 2SC2336B

DESCRIPTION

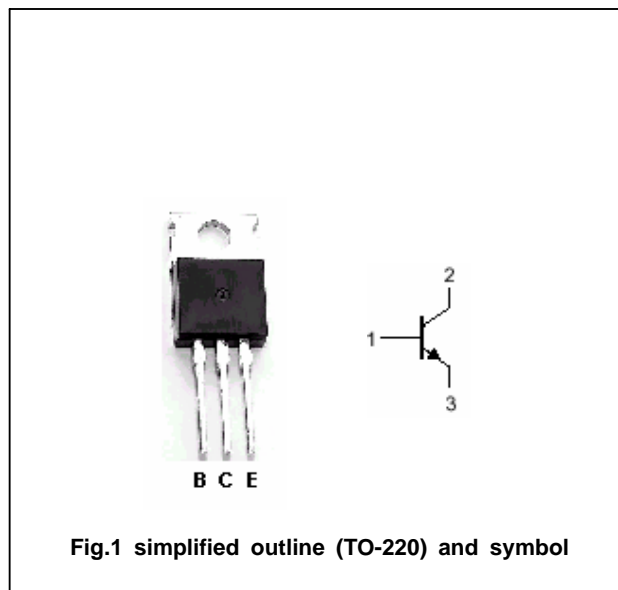
- With TO-220 package
- Complement to type 2SA1006, 2SA1006A,2SA1006B

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC2336	180	V
		2SC2336A	200	
		2SC2336B	250	
V_{CEO}	Collector-emitter voltage	2SC2336	180	V
		2SC2336A	200	
		2SC2336B	250	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_{CM}	Collector current-peak		3.0	A
P_T	Total power dissipation	$T_a=25$	1.5	W
		$T_c=25$	25	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

$T_j=25$ unless otherwise specified

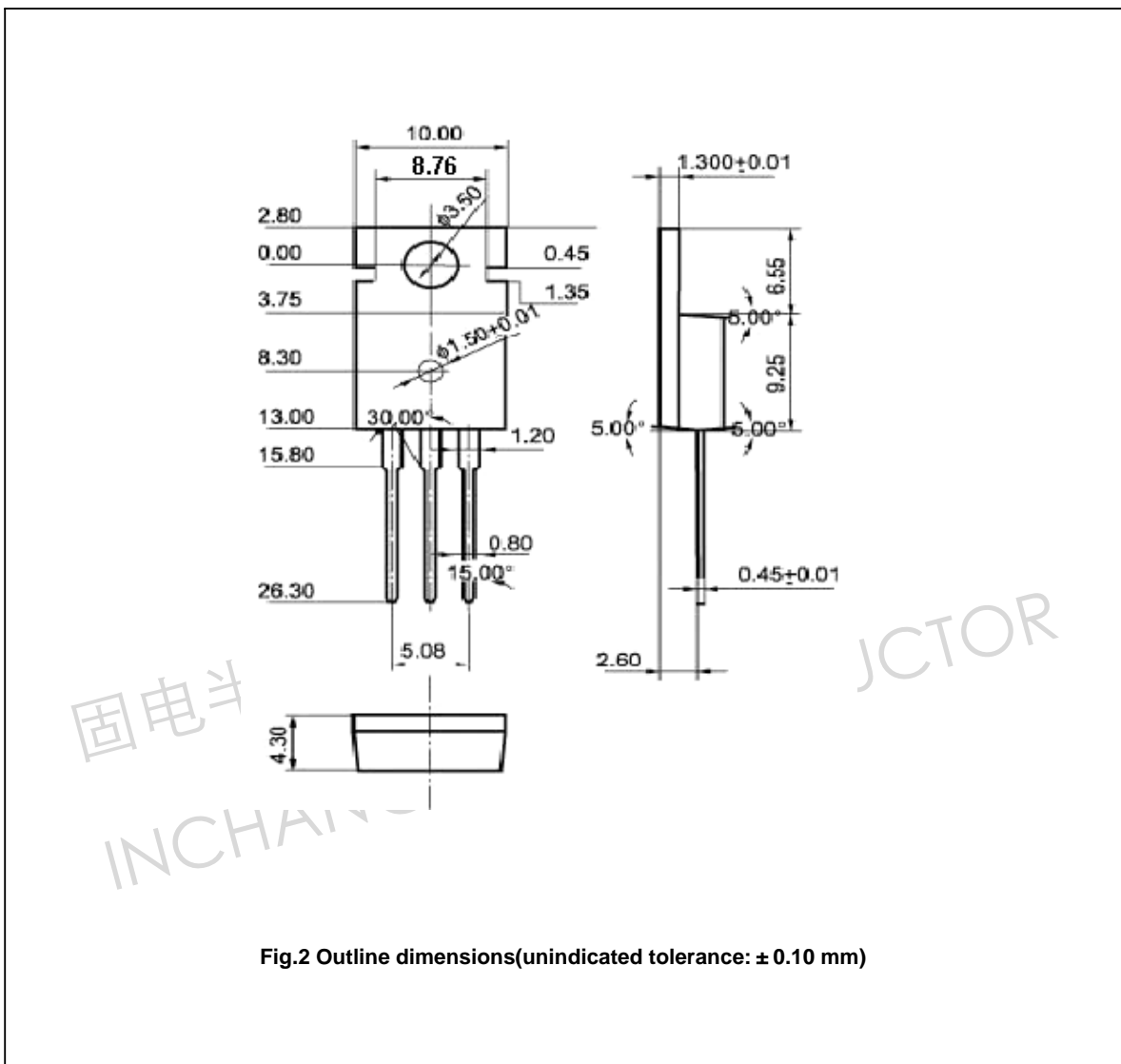
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=0.5A; I_B=50mA$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=0.5A; I_B=50mA$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=150V; I_E=0$			1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=3V; I_C=0$			1	μA
h_{FE-1}	DC current gain	$I_C=5mA; V_{CE}=5V$	30			
h_{FE-2}	DC current gain	$I_C=150mA; V_{CE}=5V$	60		320	
C_{ob}	Output capacitance	$I_E=0; V_{CB}=10V, f=1MHz$		30		pF
f_T	Transition frequency	$I_C=100mA; V_{CE}=10V$		95		MHz

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE



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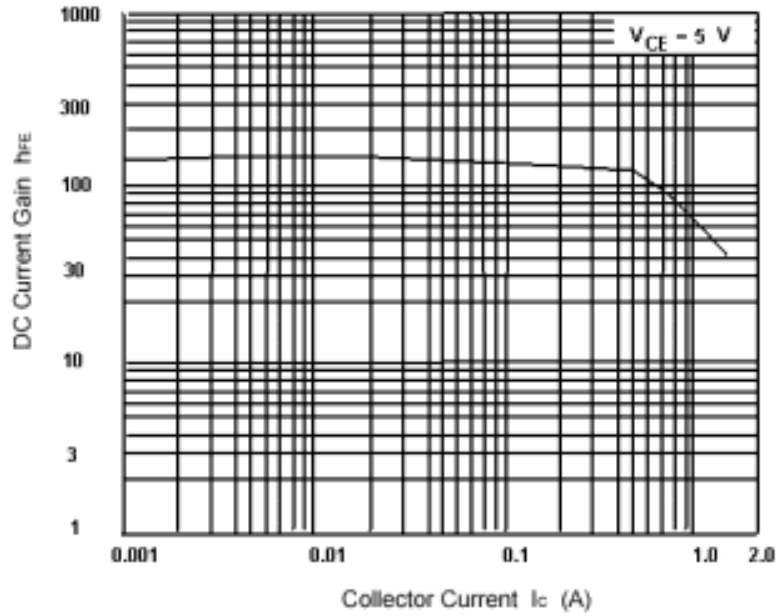


Fig.3 DC current Gain

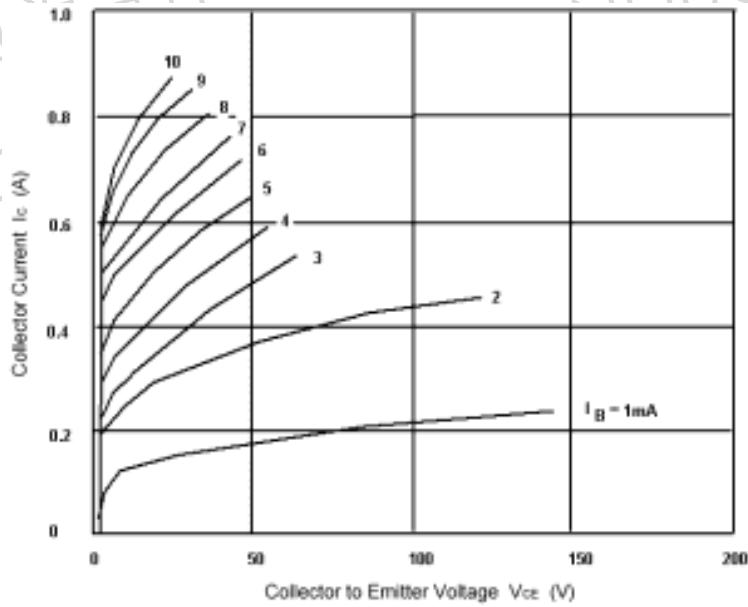


Fig.4 Static Characteristic

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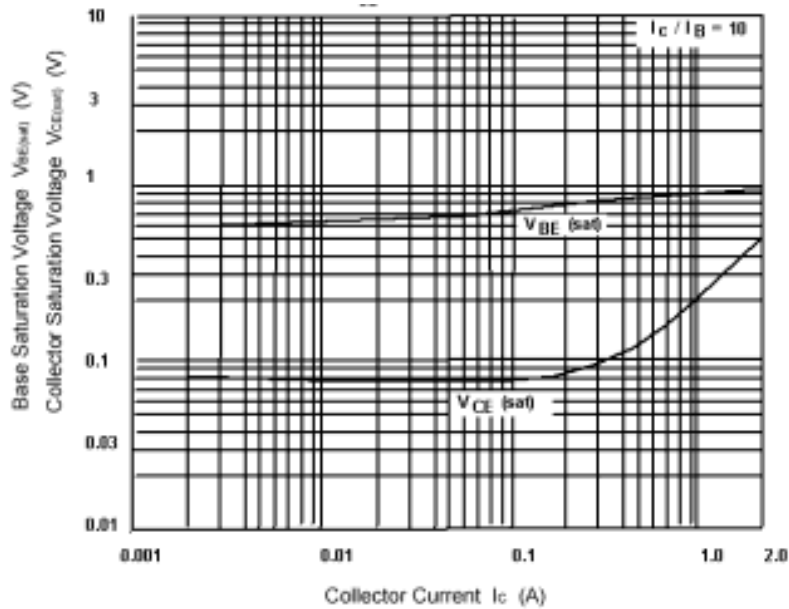


Fig.5 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

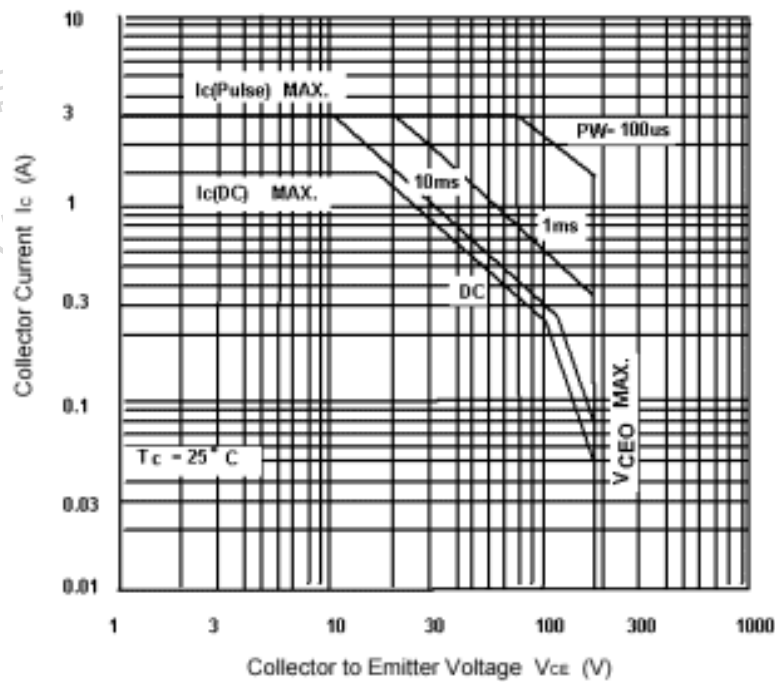


Fig.6 Safe Operating Area